



BC847C Transistor(NPN)

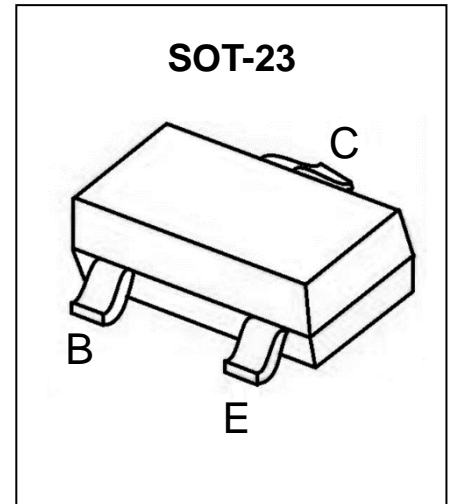
Feature

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

Marking: 1G

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current -Continuous	I _c	0.1	A
Collector Power Dissipation	P _c	0.4	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C



ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =100μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _c =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =50V, I _E =0V			100	nA
Collector cut-off current	I _{CEO}	V _{CE} =45V, I _B =0V			100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _c =0V			100	nA
DC current gain	h _{FE}	V _{CE} =5V, I _c =1mA	420		800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =100mA, I _B = 5mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =100mA, I _B = 5mA			1.1	V
Transition frequency	f _T	V _{CE} = 5V, I _c =10mA, f =100MHz	100			MHZ

Typical Characteristics

